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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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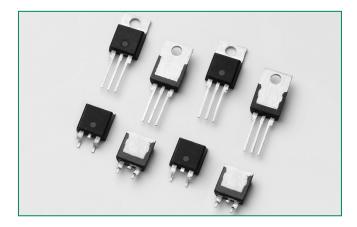




HS4040xAQx Series

AUTOMOTIVE GRADE

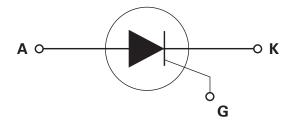
RoHS



Main Features

Symbol	Value	Unit
I _{T(RMS)}	40	А
V _{DRM} /V _{RRM}	400	V
I _{GT}	15 to 65	mA

Schematic Symbol



Description

The HS4040xAQx series of SCRs offer fast turn-off time (tq) characteristics required for applications such as power inverters, switching regulator, and high frequency pulse circuits.

These fast turn-off time SCRs offer high dv/dt and high di/dt characteristics required in higher frequency (>1000 PPS) switching circuits and a higher temperature environment.

Features & Benefits

- RoHS compliant
- Voltage capability up to 400 V
- Surge capability up to 520 A
- TO-220 and TO-263 packages
- AEC-Q101 Fully compliant
- 150°C maximum junction temperature

Applications

Fast turn-off time SCRs are ideal for multi phase voltage regulator circuits, DC/AC inverters, and higher frequency pulsing power supplies.

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit	
I _{T(RMS)}	RMS on-state current	T _c = 115°C	40	А	
I _{T(AV)}	Average on-state current	T _C = 115°C	25.0	А	
1	Peak non-repetitive surge current	single half cycle; f = 50Hz; T _J (initial) = 25°C	430	А	
I _{TSM}	r cux non repetitive surge current	single half cycle; f = 60Hz; T _J (initial) = 25°C	520		
l²t	l²t Value for fusing	$t_p = 8.3 \text{ ms}$	1122	A ² s	
di/dt	Critical rate of rise of on-state current	f = 60Hz ; T _J = 150°C	175	A/µs	
I _{GM}	Peak gate current	T _J = 150°C	3.5	А	
P _{G(AV)}	Average gate power dissipation	T _J = 150°C	0.8	W	
T _{stg}	Storage temperature range		-40 to 150	°C	
T _J	Operating junction temperature range		-40 to 150	°C	
$V_{\rm DSM}/V_{\rm RSM}$	Peak non-repetitive blocking voltage	Pw=100 μs	500	V	

Electrical Characteristics (T₁ = 25°C, unless otherwise specified)

Symbol	Test Conditions	HS4040xAQ	HS4040xAQ2	HS4040xAQ3	Unit	
		MAX.	35	45	65	mA
I _{GT}	$V_D = 12V; R_L = 30 \Omega$	MIN.	15	30	38	mA
V _{GT}		MAX.		1.5		V
I _{GT}	$V_{D} = 12V; R_{L} = 30\Omega; T_{J} = -40^{\circ}C$	MAX.	75	95	160	mA
dv/dt	$V_D = V_{DRM}$; gate open; $T_J = 150$ °C	MIN.	550		V/µs	
$V_{\rm GD}$	$V_D = V_{DRM}$; $R_L = 3.3 \text{ k}\Omega$; $T_J = 150^{\circ}\text{C}$	MIN.	0.2		V	
I _H	$I_{T} = 400 \text{mA (initial)}$	MAX.	70	120	200	mA
t _q	$I_{\rm T}$ =0.5A; $t_{\rm p}$ =50 μ s; dv/dt=5V/ μ s; di/dt=-30A/ μ s	MAX.	15	12	5	μs
t _{gt}	$I_{G} = 2 \times I_{GT}$; PW = 15 μ s; $I_{T} = 80A$	TYP.		3.0	3.5	μs

Static Characteristics

Symbol	Test Conditions			HS4040xAQ	HS4040xAQ2	HS4040xAQ3	Unit
V _{TM}	$I_{T} =$	$I_{_{\rm T}}$ = 80A; $t_{_{\rm p}}$ = 380µs MAX.			1.6	1.8	V
		T _J = 25°C		10			
I _{DRM} / I _{RRM}	V _{DRM} / V _{RRM}	T _J = 125°C	MAX.	2000			μΑ
		T _J = 150°C		4000			

Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	0.6	°C/W

Figure 1: Normalized DC Holding Current vs. Junction Temperature

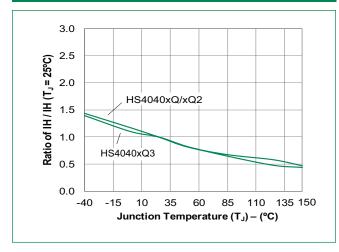


Figure 2: Normalized DC Gate Trigger Current vs. Junction Temperature

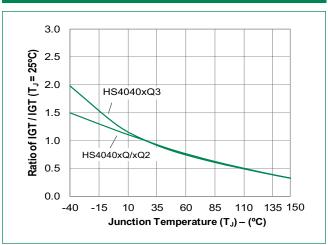




Figure 3: Normalized DC Gate Trigger Voltage vs.
Junction Temperature

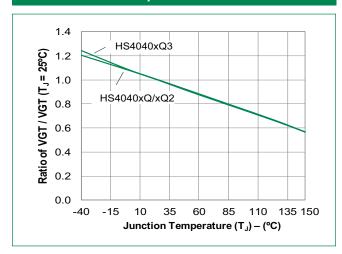


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

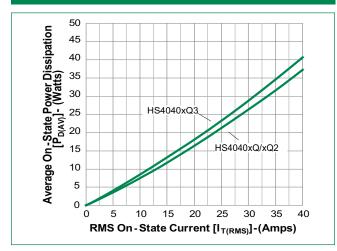


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

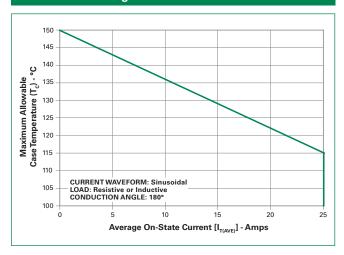


Figure 4: On-State Current vs. On-State Voltage (Typical)

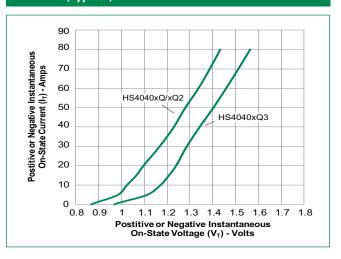


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current

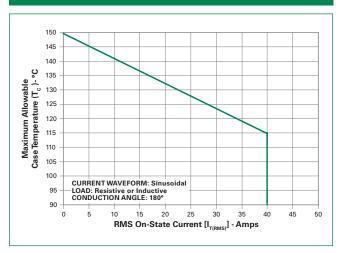


Figure 8: Peak Capacitor Discharge Current

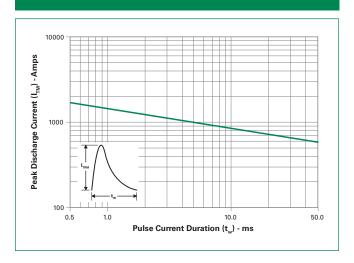




Figure 9: Peak Capacitor Discharge Current Derating

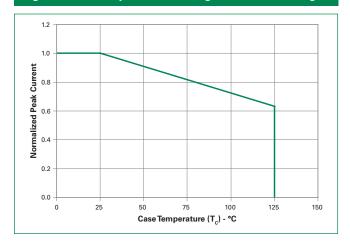
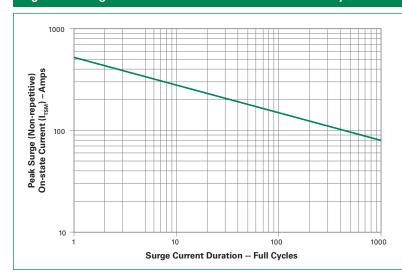


Figure 10: Surge Peak On-State Current vs. Number of Cycles



SUPPLY FREQUENCY: 60 Hz Sinusoidal

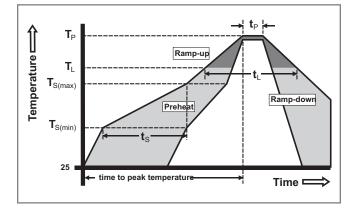
LOAD: Resistive

RMS On-State Current: [$I_{T(RMS)}$]: Maximum Rated Value at Specified Case Temperature

- 1. Gate control may be lost during and immediately following surge current interval.
- 2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Condition		Pb – Free assembly
	-Temperature Min (T _{s(min)})	150°C
Pre Heat	-Temperature Max (T _{s(max)})	200°C
	-Time (min to max) (t _s)	60 - 180 secs
Average ramp up rate (Liquidus Temp) (T _L) to peak		5°C/second max
T _{S(max)} to T _L	- Ramp-up Rate	5°C/second max
Reflow	-Temperature (T _L) (Liquidus)	217°C
Reliow	-Temperature (t _L)	60 – 150 seconds
PeakTemp	perature (T _P)	260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t _p)		20 - 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C	to peakTemperature (T _P)	8 minutes Max.
Do not exc	ceed	280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated	
Body Material	UL recognized epoxy meeting flammability classification V-0	
Lead Material	Copper Alloy	

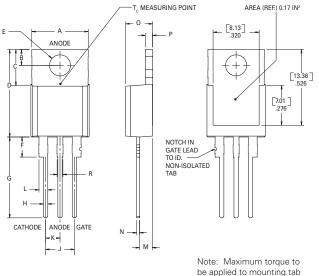
Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 150°C for 1008 hours
Biased Temperature & Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
Temperature Cycling	JESD22 A-104 Appendix 6 -55°C to 150°C, 15-minute dwell, 1000 cycles
Intermittent Operational Life	T _A =25C, ΔT _J ≥ 100°C, 1008hrs
Autoclave (Pressure Cooker Test)	EIA/JEDEC: JESD22-A102 121°C, 100%RH, 15psig, 96hours
Resistance to Solder Heat	JESD22 A-111: 260°C, 10 seconds
Solderability	ANSI/J-STD-002, category 3, Test A

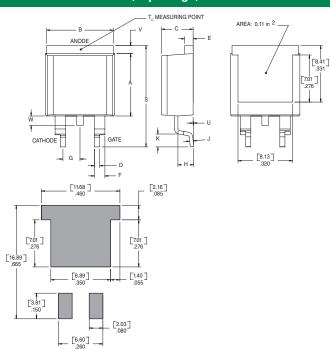
Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



be applied to mounting tab is 8 in-lbs. (0.904 Nm).

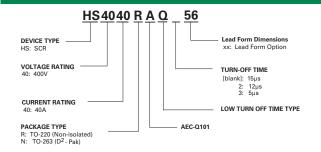
Dimension	Inc	hes	Millin	neters
Dimension	Min	Max	Min	Max
А	0.380	0.420	9.65	10.67
В	0.105	0.115	2.67	2.92
С	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
Е	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
Н	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
М	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
0	0.178	0.188	4.52	4.78
Р	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions - TO- 263 (N-package) - D2-Pak Surface Mount



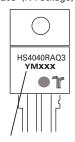
Dimension	Inches		Millin	neters
Dimension	Min	Max	Min	Max
А	0.360	0.370	9.14	9.40
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.63	0.89
Е	0.048	0.055	1.22	1.40
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
Н	0.083	0.093	2.11	2.36
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.87
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Part Numbering System



Part Marking System

TO-220 AB - (R Package) TO-263 (N Package)



Date Code Marking Y:Year Code M: Month Code XXX: Lot Trace Code

Product Selector

Part Number	Voltage	Gate Sensitivity	Туре	Package	
rait ivuilibei	400V	Gate Sensitivity	Туре	r ackage	
HS4040RAQ	X	15-35	Standard SCR	TO-220AB	
HS4040NAQ	X	15-35	Standard SCR	TO-263	
HS4040RAQ2	X	30-45	Standard SCR	TO-220AB	
HS4040NAQ2	X	30-45	Standard SCR	TO-263	
HS4040RAQ3	X	38-65	Standard SCR	TO-220AB	
HS4040NAQ3	X	38-65	Standard SCR	TO-263	

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
HS4040RAQTP	HS4040RAQ	2.2g	Tube	500 (50 per tube)
HS4040RAQ2TP	HS4040RAQ2	2.2g	Tube	500 (50 per tube)
HS4040RAQ3TP	HS4040RAQ3	2.2g	Tube	500 (50 per tube)
HS4040NAQRP	HS4040NAQ	1.6g	Embossed Carrier	500
HS4040NAQ2RP	HS4040NAQ2	1.6g	Embossed Carrier	500
HS4040NAQ3RP	HS4040NAQ3	1.6g	Embossed Carrier	500

Reel Pack (RP) for TO-263 Embossed Carrier Specifications

Meets all EIA-481-2 Standards

